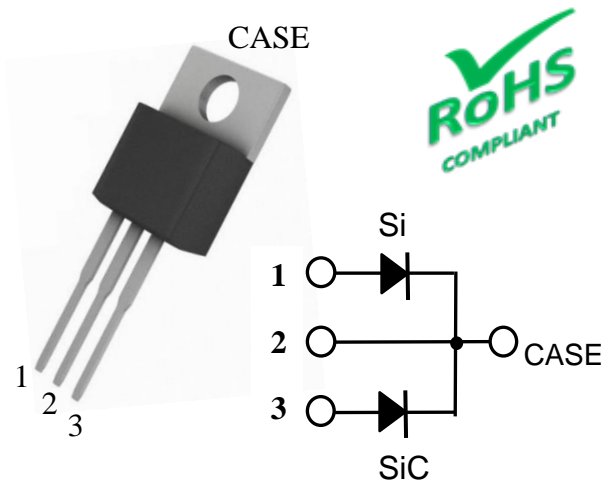


Features

- Co-packaged surge bypass diode
- 175°C SiC maximum operating junction temperature
- Extremely fast switching not dependent on temperature
- Essentially no reverse or forward recovery
- Positive temperature coefficient for safe operation and ease of paralleling
- RoHS compliant



Typical Applications

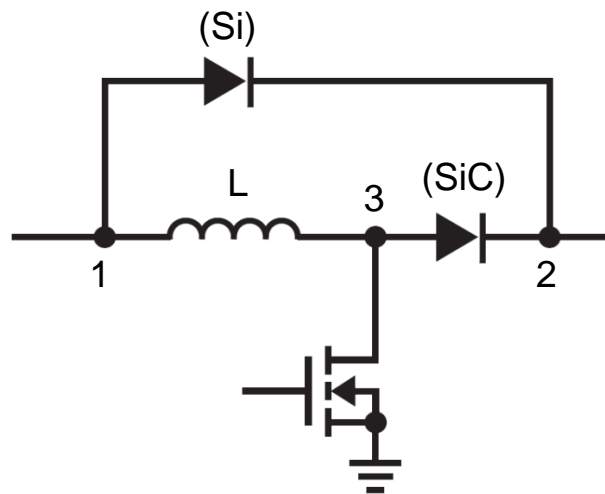
- Power converters
- Switching-mode power supplies
- Power factor correction modules

Part Number	Package	Marking
UJDS06508T	TO-220-3	UJDS06508T

Descriptions

United Silicon Carbide, Inc offers the xR series of high-performance SiC Schottky diodes. With zero reverse recovery charge and 175°C maximum junction temperature, USCI's diodes are ideally suited for high-frequency and high-efficiency power systems with minimum cooling requirements. This product co-packages a surge bypass silicon diode to reduce component count in PFC circuits.

Typical Connection in a PFC Circuit



Maximum Ratings

SiC Schottky Diode

Parameter	Symbol	Test Conditions	Value	Units
DC Blocking Voltage	V_{DC}		650	V
Repetitive Peak Reverse Voltage, $T_j=25^\circ\text{C}$	V_{RRM}		650	V
Surge Peak Reverse Voltage	V_{RSM}		650	V
Maximum DC Forward Current	I_F	$T_C = 132^\circ\text{C}$	8	A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_C = 25^\circ\text{C}$, 8.3ms Half Sine Pulse	44	A
Non-Repetitive Peak Forward Current	$I_{F,max}$	$T_C = 25^\circ\text{C}$, 10 μs	385	A
Non-Repetitive Avalanche Energy	E_{AS}	$T_j = 25^\circ\text{C}$, $L = 5\text{mH}$, $I_{pk}=5.5\text{A}$, $V_{DD}=100\text{V}$	67	mJ
Power Dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	62	W
		$T_C = 132^\circ\text{C}$	18	
Maximum Junction Temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and Storage Temperature	T_j, T_{STG}		-55 to 175	$^\circ\text{C}$

Si Diode

Parameter	Symbol	Test Conditions	Value	Units
DC Blocking Voltage	V_{DC}		600	V
Repetitive Peak Reverse Voltage, $T_j=25^\circ\text{C}$	V_{RRM}		600	V
Surge Peak Reverse Voltage	V_{RSM}		600	V
Maximum DC Forward Current	I_F	$T_C = 150^\circ\text{C}$	10	A
Non-Repetitive Forward Surge Current	I_{FSM}	$T_C = 25^\circ\text{C}$, 8.3ms Half Sine Pulse	100	A
Non-Repetitive Peak Forward Current	$I_{F,max}$	$T_C = 25^\circ\text{C}$, 10 μs	750	A
Power Dissipation	P_{Tot}	$T_C = 25^\circ\text{C}$	107	W
		$T_C = 150^\circ\text{C}$	17	
Maximum Junction Temperature	$T_{J,max}$		175	$^\circ\text{C}$
Operating and Storage Temperature	T_j, T_{STG}		-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	symbol	Component	Value			Units
			Min	Typ	Max	
Thermal Resistance	$R_{\theta JC}$	SiC Diode			2.4	$^\circ\text{C}/\text{W}$
Thermal Resistance	$R_{\theta JC}$	Si Diode			1.4	$^\circ\text{C}/\text{W}$

Electrical Characteristics

SiC Schottky Diode ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward Voltage	V_F	$I_F = 8\text{A}, T_J = 25^\circ\text{C}$	-	1.5	1.7	V
		$I_F = 8\text{A}, T_J = 150^\circ\text{C}$	-	1.8	2.1	
		$I_F = 8\text{A}, T_J = 175^\circ\text{C}$	-	1.95	2.25	
Reverse Current	I_R	$V_R = 650\text{V}, T_J = 25^\circ\text{C}$	-	20	230	μA
		$V_R = 650\text{V}, T_J = 175^\circ\text{C}$	-	40	700	
Total Capacitive Charge	Q_C	$V_R = 400\text{V}, I_F = 8\text{A},$ $di/dt = 250\text{A}/\mu\text{s}$		13		nC
Total Capacitance	C	$V_R = 1\text{V}, f = 1\text{MHz}$		260		pF
		$V_R = 300\text{V}, f = 1\text{MHz}$		29		
		$V_R = 600\text{V}, f = 1\text{MHz}$		23		

Si Diode ($T_J = +25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test Conditions	Value			Units
			Min	Typ	Max	
Forward Voltage	V_F	$I_F = 10\text{A}, T_J = 25^\circ\text{C}$	-	1.4	-	V
		$I_F = 10\text{A}, T_J = 150^\circ\text{C}$	-	1.16	1.38	
		$I_F = 10\text{A}, T_J = 175^\circ\text{C}$	-	1.12	1.34	
Reverse Current	I_R	$V_R = 600\text{V}, T_J = 25^\circ\text{C}$	-	-	10	μA
		$V_R = 600\text{V}, T_J = 150^\circ\text{C}$	-	-	250	
Reverse Recovery Time	t_{rr}	$V_R = 30\text{V}, I_F = 1\text{A},$ $di/dt = 50\text{A}/\mu\text{s},$ Ramp Recovery	-	-	75	ns
		$V_R = 30\text{V}, I_F = 1\text{A},$ $di/dt = 100\text{A}/\mu\text{s},$ Ramp Recovery	-	35	-	

Typical Performance
SiC Schottky Diode

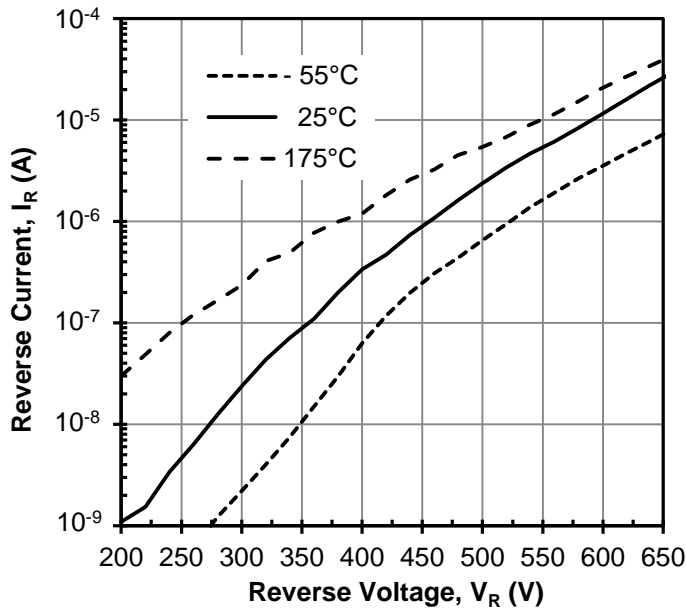


Figure 1 Typical reverse characteristics

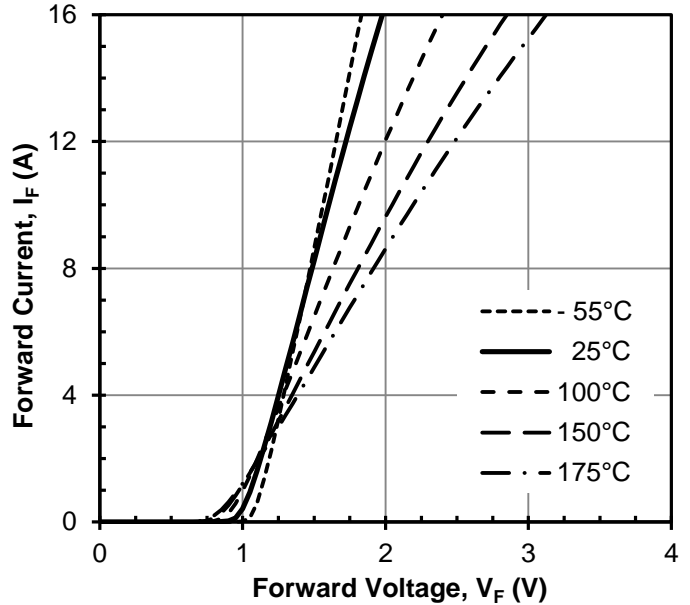


Figure 2 Typical forward characteristics

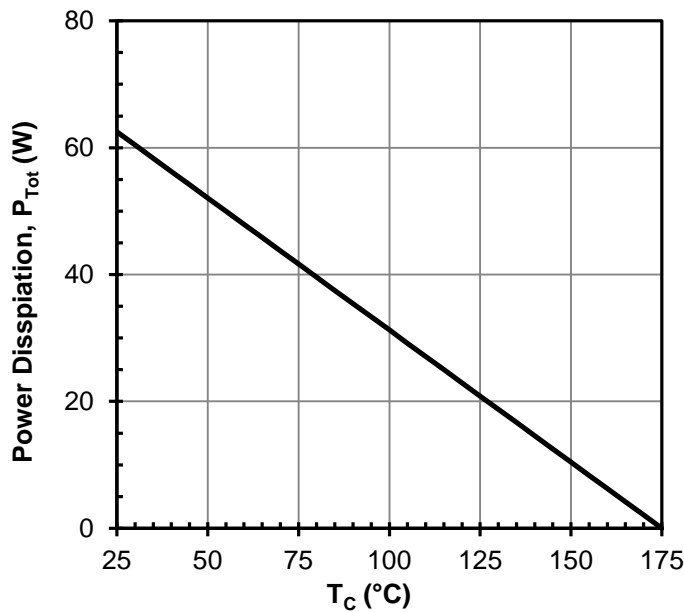


Figure 3 Power dissipation

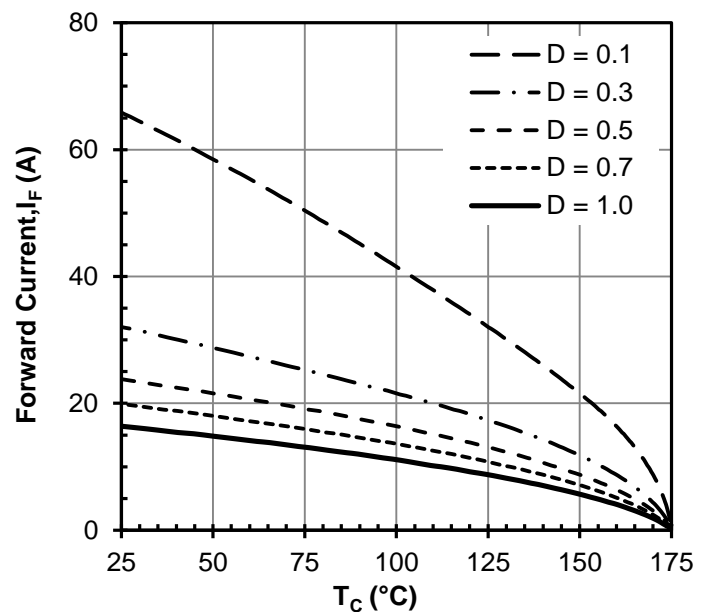


Figure 4 Diode forward current

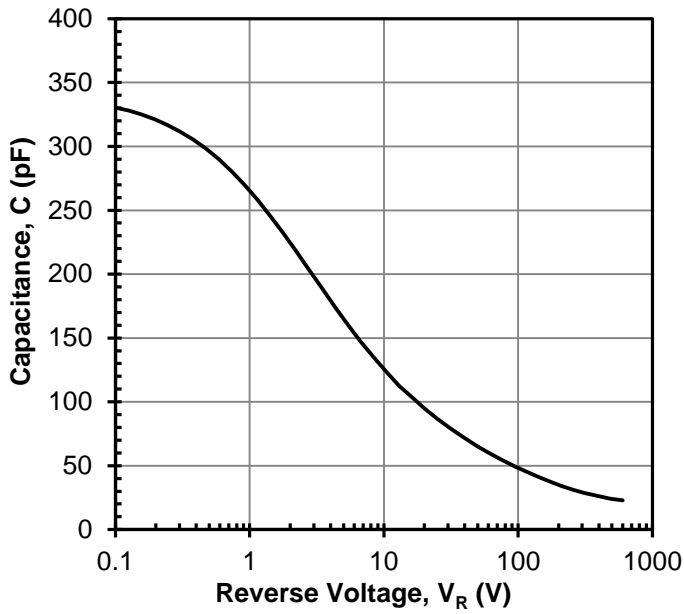


Figure 5 Capacitance vs. reverse voltage

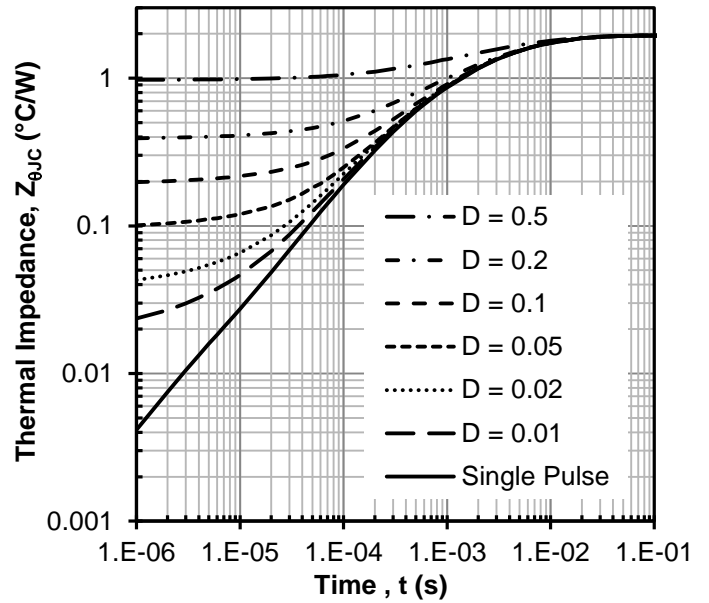


Figure 6 Transient thermal impedance

Si Diode

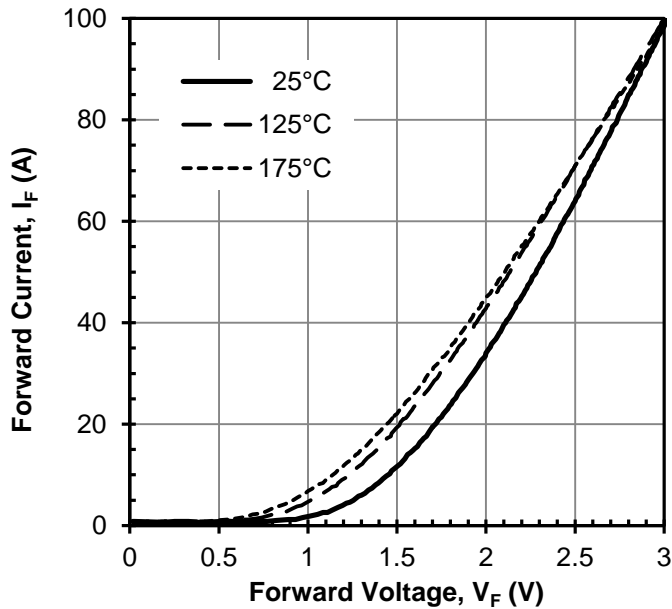
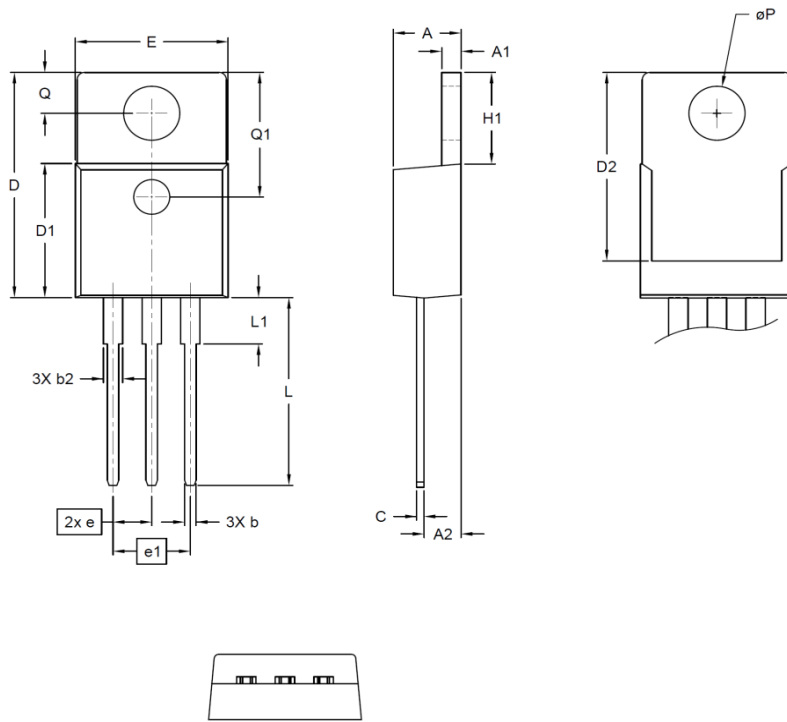


Figure 7 Typical forward characteristics

Mechanical Characteristics



	INCH			MILLIMETER		
	MIN	NOM	MAX	MIN	NOM	MAX
A	.140	.175	.190	3.56	4.45	4.83
A1	.020	.050	.055	0.51	1.27	1.40
A2	.080	.096	.115	2.03	2.44	2.92
b	.015	.030	.040	0.38	7.62	1.02
b2	.040	.050	.070	1.02	1.27	1.78
C	.014	.019	.030	0.36	0.48	0.76
D	.560	.605	.650	14.22	15.37	16.51
D1	.330	.360	.370	8.38	9.14	9.40
D2	.480	.507	.517	12.19	12.88	13.13
E	.380	.386	.420	9.65	9.80	10.67
e	.100 BSC.			2.54 BSC.		
e1	.200 BSC.			5.08 BSC.		
L	.495	.505	.580	12.57	12.82	14.73
L1	---	.125	.250	---	3.18	6.35
øP	.139	.145	.161	3.53	3.68	4.09
H1	.230	.245	.270	5.84	6.22	6.86
Q	.100	.110	.135	2.54	2.79	3.43
Q1	.330	.335	.340	8.38	8.51	8.64

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